

Description

The PSJMDP60R1000 is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

MOSFET Product Summary

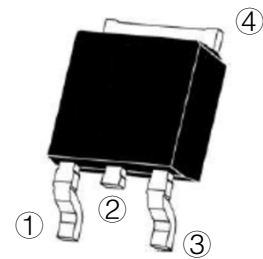
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
600	785 @ $V_{GS} = 10V$	3.3

Feature

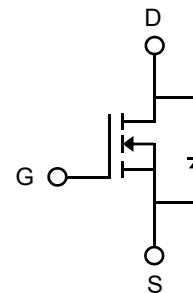
- Fast Switching Capability
- Lead free product is acquired.
- Avalanche Energy Tested

Applications

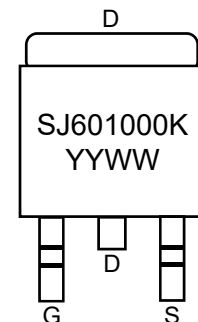
- PWM applications
- Load Switch
- Power Management
- DC-DC Converters



TO-252 (Top View)



Circuit Diagram



Marking (Top View)

Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	± 30	V
Drain Current-Continuous ¹⁾	$T_C = 25^\circ C$	I_D	3.3	A
	$T_C = 100^\circ C$		2.1	
Pulsed Drain Current ²⁾		I_{DM}	7.0	A
Total Power Dissipation ³⁾		P_D	54.3	W
Avalanche Current ⁴⁾		I_{AS}	1.5	A
Avalanche Energy ⁴⁾		E_{AS}	21.5	mJ
Thermal Resistance , Junction-to-Case ⁵⁾		$R_{\theta JC}$	2.3	$^\circ C/W$
Thermal Resistance , Junction-to-Ambient ⁶⁾		$R_{\theta JA}$	52	$^\circ C/W$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ C$

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V,I _D = 250μA	600	700	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 600V,V _{GS} = 0V	-	-	1.0	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±30V,V _{DS} = 0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} ,I _D = 250μA	2.5	2.9	3.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V,I _D = 1A	-	785	1008	mΩ
Dynamic Characteristics ⁷⁾						
Input Capacitance	C _{iss}	V _{DS} = 100V,V _{GS} = 0V, f = 1.0MHz	-	232.7	-	pF
Output Capacitance	C _{oss}		-	11.5	-	
Reverse Transfer Capacitance	C _{rss}		-	0.8	-	
Switching Characteristics ⁷⁾						
Turn-on Delay Time	t _{d(on)}	V _{DS} = 400V, V _{GS} = 10V, I _D = 1A,R _G = 10Ω	-	9.7	-	ns
Turn-on Rise Time	t _r		-	8.1	-	
Turn-Off Delay Time	t _{d(off)}		-	29.3	-	
Turn-Off Fall Time	t _f		-	34.5	-	
Total Gate Charge	Q _g	V _{DS} = 480V, V _{GS} = 10V, I _D = 1A	-	6.4	-	nC
Gate-Source Charge	Q _{gs}		-	1.1	-	
Gate-Drain Charge	Q _{gd}		-	2.5	-	
Gate Resistance	R _g	f=1MHz , Open Drain	-	5.6	-	Ω
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V,I _S = 1A	-	0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F =1A, V _R =200V, dI _F /d _t =100A/μs	-	102	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	430.7	-	μC
Peak Reverse Recovery Current	I _{rrm}		-	8.45	-	A

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature($T_{J_Max}=150^\circ C$).
3. Pulse Test: Pulse Width $\leq 10\mu s$, Duty Cycle $\leq 1\%$.
4. This single-pulse measurement was taken under the following condition [$L=20mH, V_{GS}=10V, V_{DS}=100V$]while it's value is limited by $T_{J_Max}=150^\circ C$.
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on infinite heatsink.
7. Guaranteed by design, not subject to production.

Typical Characteristics

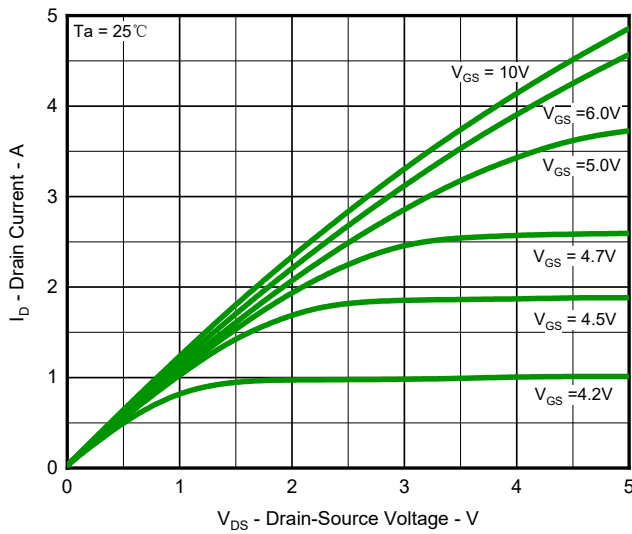


Fig.1 Output Characteristics

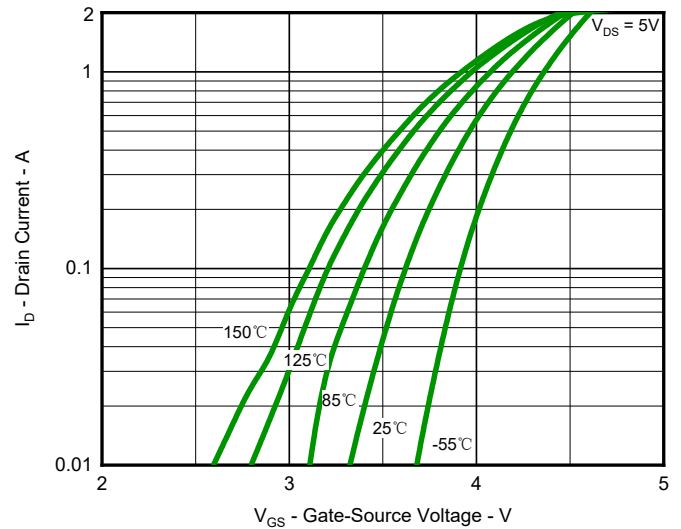


Fig.2 Typical Transfer Characteristic

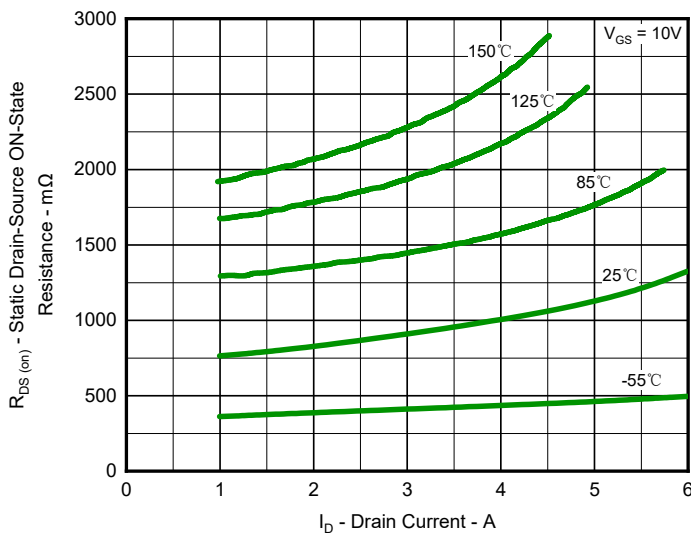


Fig.3 Typical On-Resistance vs Drain Current and Temperature

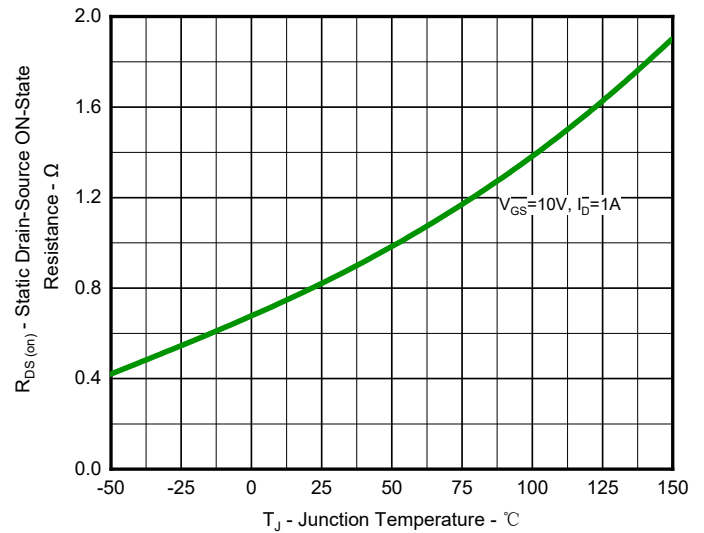


Fig.4 On-Resistance Variation with Temperature

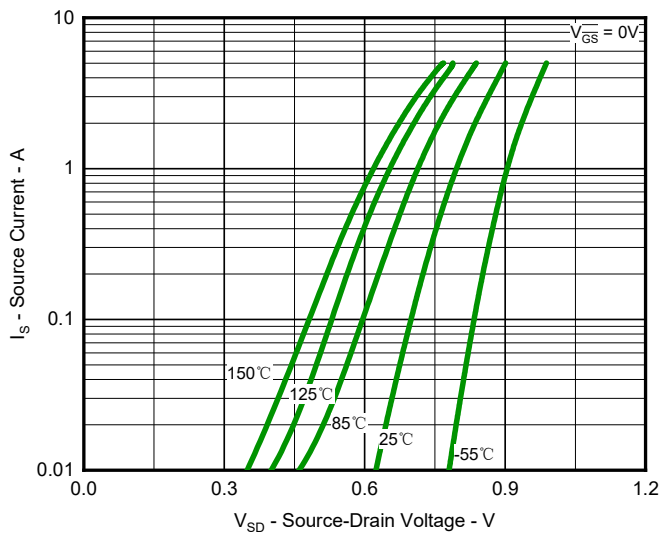


Fig.5 Diode Forward Voltage vs. Current

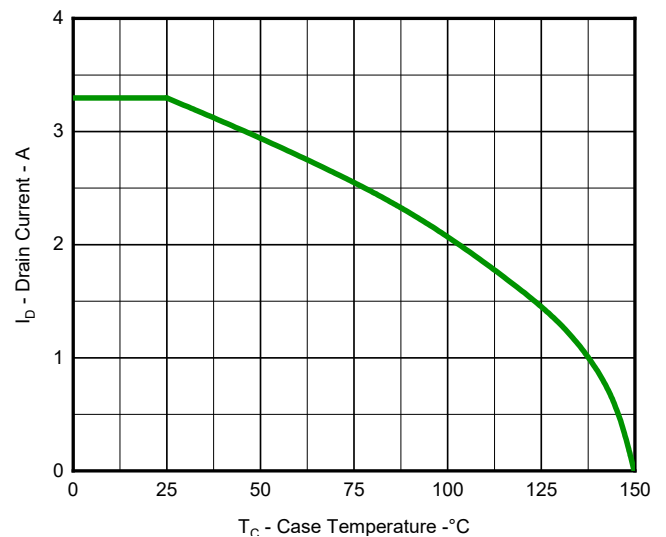


Fig.6 Maximum Drain Current vs. Case Temperature

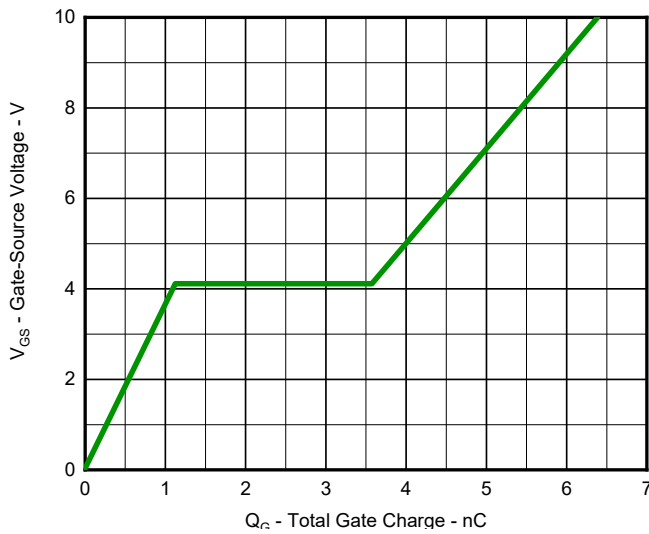


Fig.7 Gate Charge Characteristics

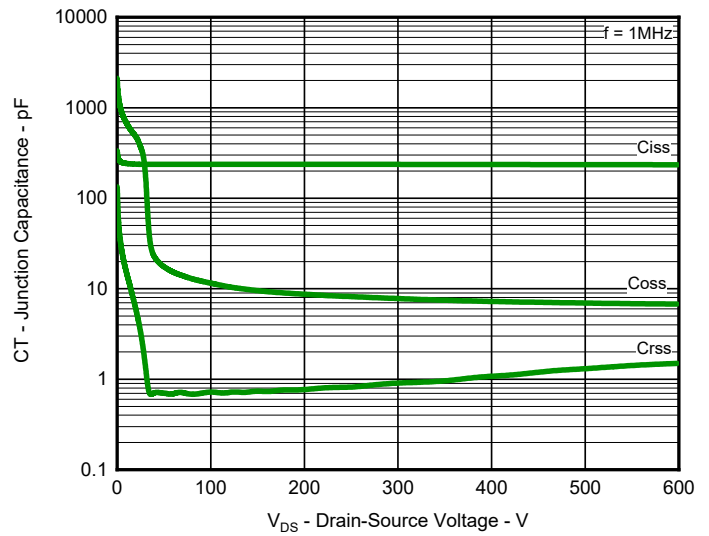


Fig.8 Typical Junction Capacitance

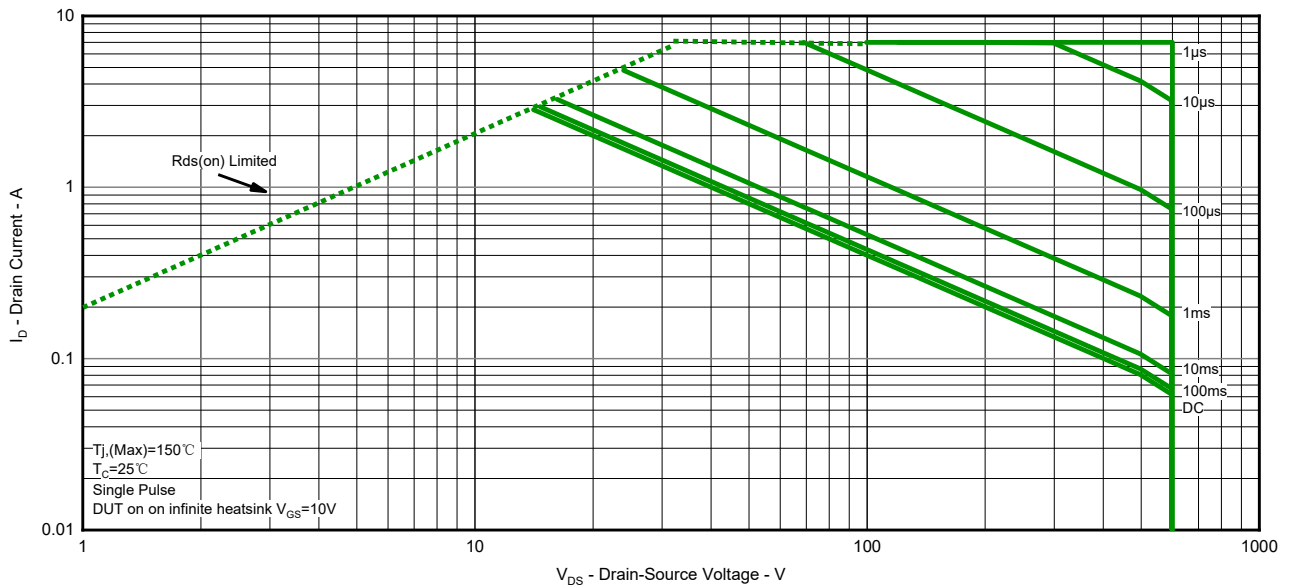


Fig.9 Safe Operation Area

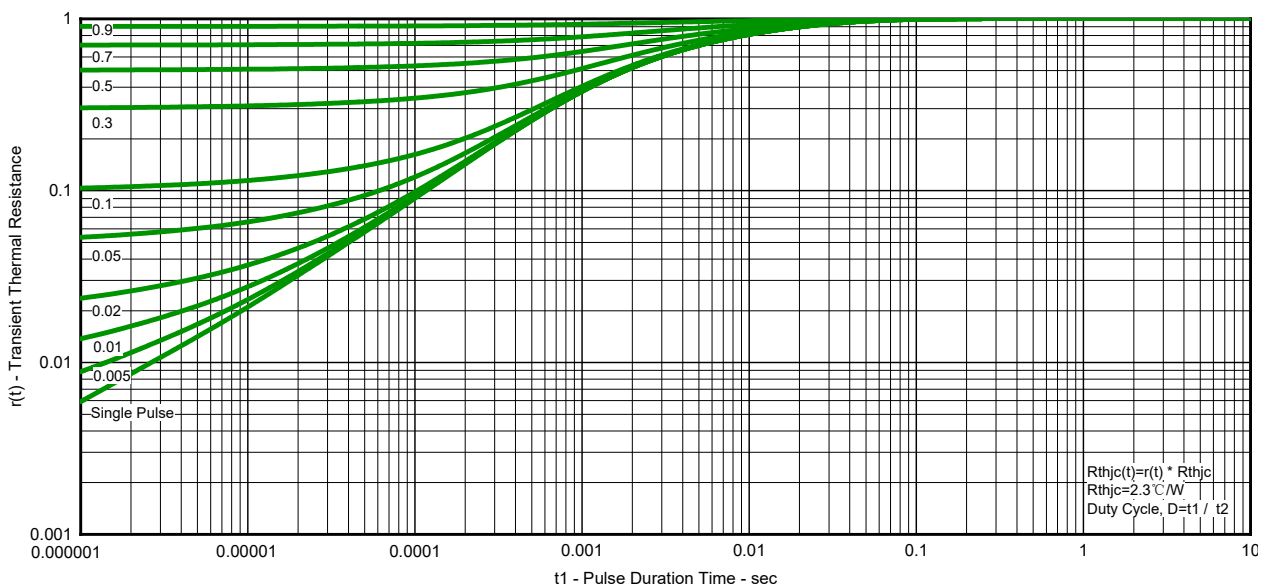
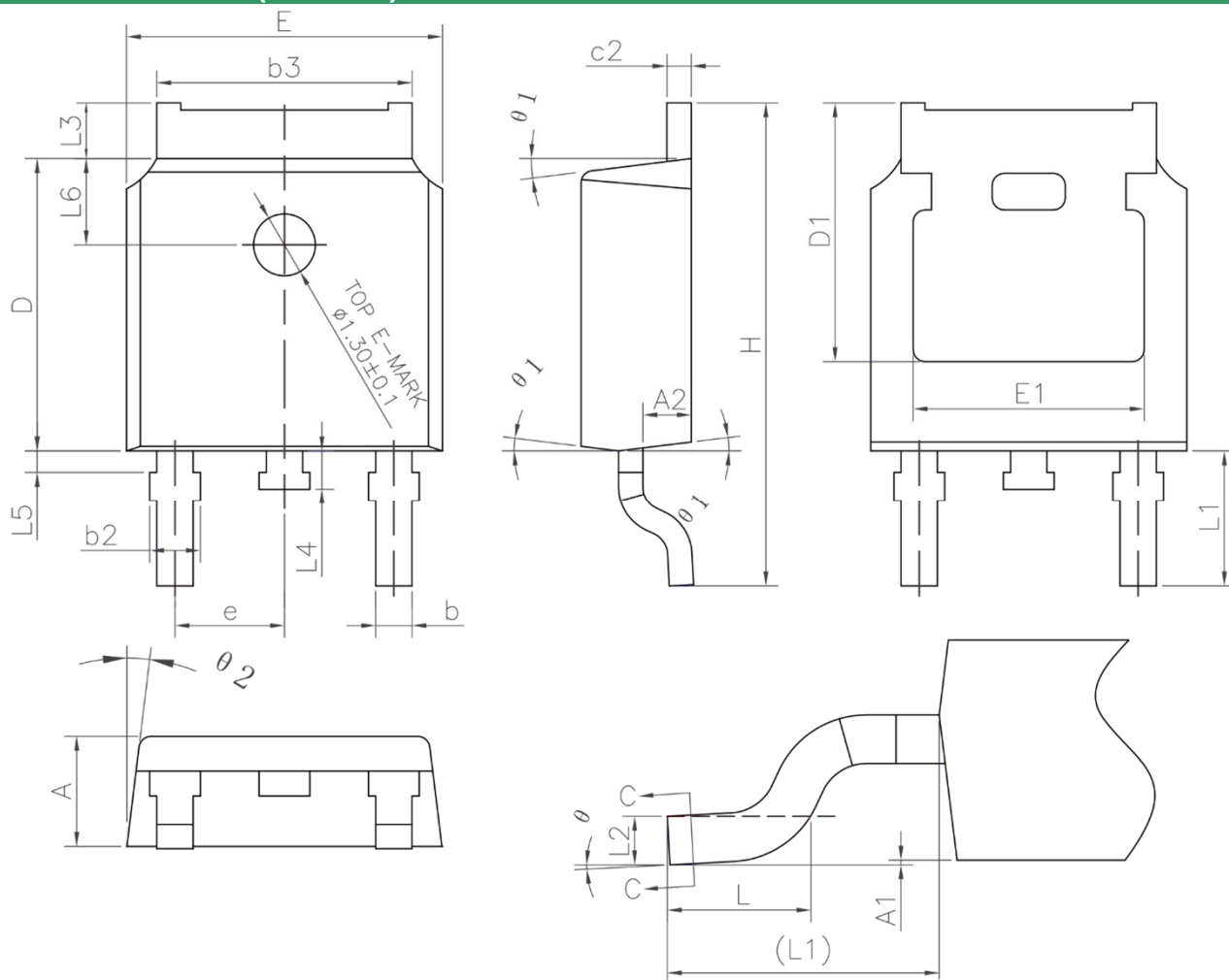


Fig.10 Transient Thermal Resistance

Product Dimension (TO-252)



Dim	Millimeters		Inches		Dim	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	2.20	2.38	0.087	0.094	e	2.186	2.386	0.086	0.094
A1	0.00	0.10	0.000	0.004	H	9.80	10.40	0.386	0.409
A2	0.90	1.10	0.035	0.043	L	1.40	1.70	0.055	0.067
b	0.72	0.82	0.028	0.032	L1	2.90 Ref.		0.114 Ref.	
b2	0.72	0.90	0.028	0.035	L2	0.508 BSC.		0.020 BSC.	
b3	5.13	5.46	0.202	0.215	L3	0.90	1.25	0.035	0.049
c	0.47	0.60	0.019	0.024	L4	0.60	1.00	0.024	0.039
c2	0.47	0.60	0.019	0.024	L5	0.15	0.75	0.006	0.030
D	6.00	6.20	0.236	0.244	L6	1.80 Ref.		0.071 Ref.	
D1	5.25	-	0.207	-	θ	0°	8°	0°	8°
E	6.50	6.70	0.256	0.264	θ1	5°	9°	5°	9°
E1	4.70	-	0.185	-	θ2	5°	9°	5°	9°

Ordering Information

Device	Package	Reel	Shipping
PSJMDP60R1000	TO-252	13"	2500 / Tape & Reel

Load With Information

